Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	100	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2		-	-	8	Α
Static characte	eristics						,
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.8	0.895	V
Dynamic chara	acteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5; Fig. 7		-	20	25	ns
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	$rac{1}{2}$	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYW29E-100	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	ı	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	100	V
V_{RWM}	crest working reverse voltage			-	100	V
V _R	reverse voltage			-	100	V
I _{F(AV)}	average forward current	\bar{o} = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2		-	8	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 128 °C; square-wave pulse		-	16	А
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		-	88	А
		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		-	80	А
I _{RRM}	repetitive peak reverse current	$\delta = 0.001 \; ; t_p = 2 \; \mu s$		-	0.2	А

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs		-	0.2	Α
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature			-	150	°C
Electrostatic discharge						
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV

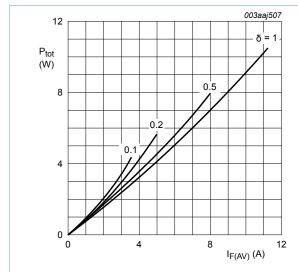


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.791 \text{ V}; R_{S} = 0.013 \text{ } \Omega \end{split}$$

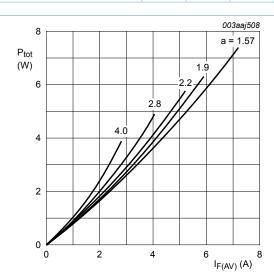


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

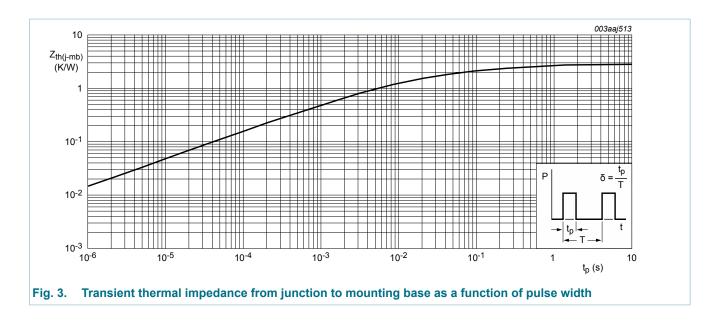
$$\begin{aligned} \mathbf{a} &= \mathbf{form} \ \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V_O} &= 0.791 \ \mathbf{V}; \ \mathbf{R_S} = 0.013 \ \Omega \end{aligned}$$

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I _R reve	reverse current	V _R = 100 V; T _j = 25 °C	-	2	10	μA
		V _R = 100 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic cl	haracteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5; Fig. 6$	-	4	11	nC
t _{rr} reverse recovery time	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; ramp recovery; <u>Fig. 5</u> ; <u>Fig. 7</u>	-	20	25	ns
		I_F = 0.5 A; I_R = 1 A; $I_{R(meas)}$ = 0.25 A; T_j = 25 °C; step recovery; Fig. 8	-	15	20	ns
V_{FRM}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; T_j = 25 °C;$ Fig. 9	-	1	-	V

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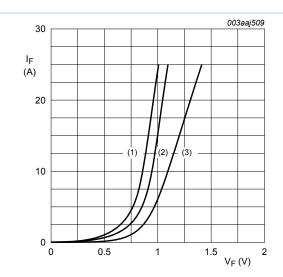


Fig. 4. Forward current as a function of forward voltage

(1) $T_i = 150$ °C; typical values;

(2) T_i = 150 °C; maximum values;

(3) $T_i = 25$ °C; maximum values;

 $V_O = 0.791 \text{ V}; R_S = 0.013 \Omega$

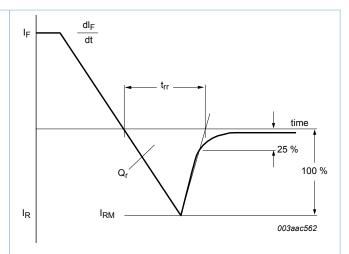


Fig. 5. Reverse recovery definitions; ramp recovery

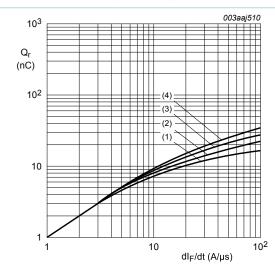


Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values

(1)
$$I_F = 1 A$$
; $T_i = 25 \, ^{\circ}\text{C}$

(2)
$$I_F = 2 A$$
; $T_j = 25 \text{ °C}$

(3)
$$I_F = 5 A$$
; $T_j = 25 \text{ °C}$

(4) $I_F = 10 A; T_i = 25 °C$

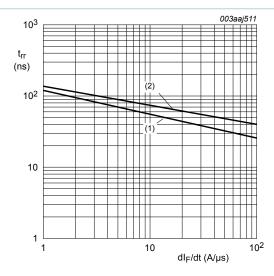
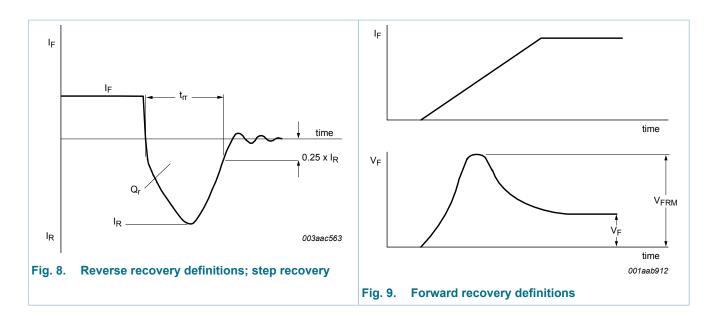


Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(1)
$$I_F = 1 A$$
; $T_i = 25 \, ^{\circ}C$

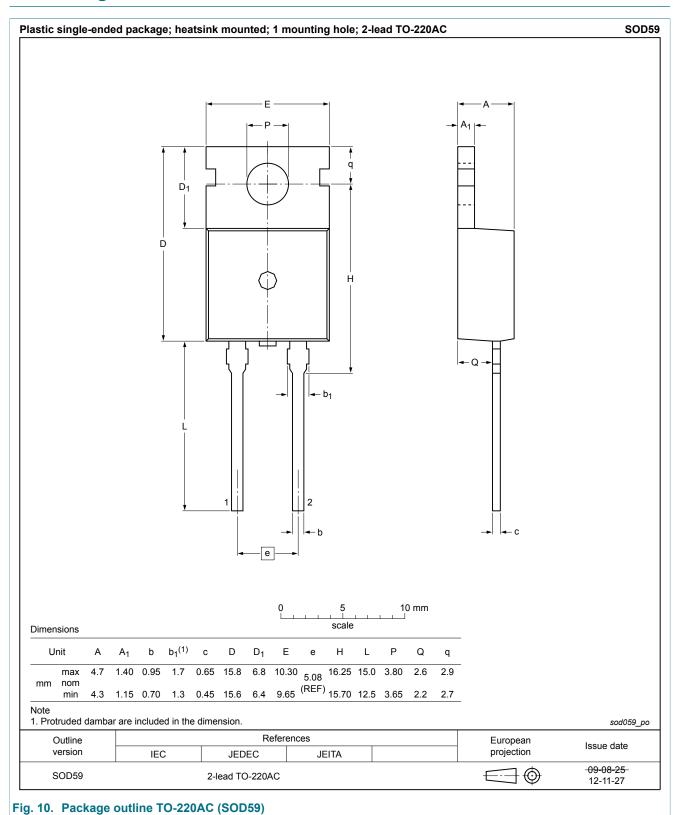
(2)
$$I_F = 10 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$$

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10. Package outline



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11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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